

# Phase-locked loop clock generator

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## SPECIFICATION

### 1 FEATURES

- TSMC CMOS 65 nm
- Low phase noise
- Low jitter
- Fully integrated 2GHz VCO
- Fully integrated loop filter with ability to use external loop filter
- Built-in lock detection circuit
- High reference frequency spur rejection
- Adjustable value of charge pump output current
- Built-in ADC for measuring VCO control voltage value
- Digital loop gain compensation
- Low current consumption
- Adjustable power supply voltage
- Supported foundries: TSMC, UMC, Global Foundries, SMIC

### 2 APPLICATION

- Low jitter clock generation

### 3 OVERVIEW

It is a integer-N phase-locked loop frequency synthesizer (PLL) based on fully integrated 2GHz LC-VCO with low gain and fine phase noise performance. It work with reference frequency from 25 MHz XTAL oscillator or external signal source with frequency up to 500 MHz. Phase-frequency divider compare frequency can be equal or 2,3,4...63 times lower than reference. VCO frequency N-divider has programmable coefficient of division with step 1 in range 4 to 2047. Phase-frequency detector has built-in analog and digital lock detector circuits. Charge pump scheme with ADC and adjustable output current allow compensation VCO gain variation within band and keep loop gain constant. Integrated low-pass loop filter has adjustable values of resistance and capacitance for tune loop and get best phase-noise performance. All of output clocks have 0.5 duty cycle value using duty cycle recovery circuit.

## 4 STRUCTURE

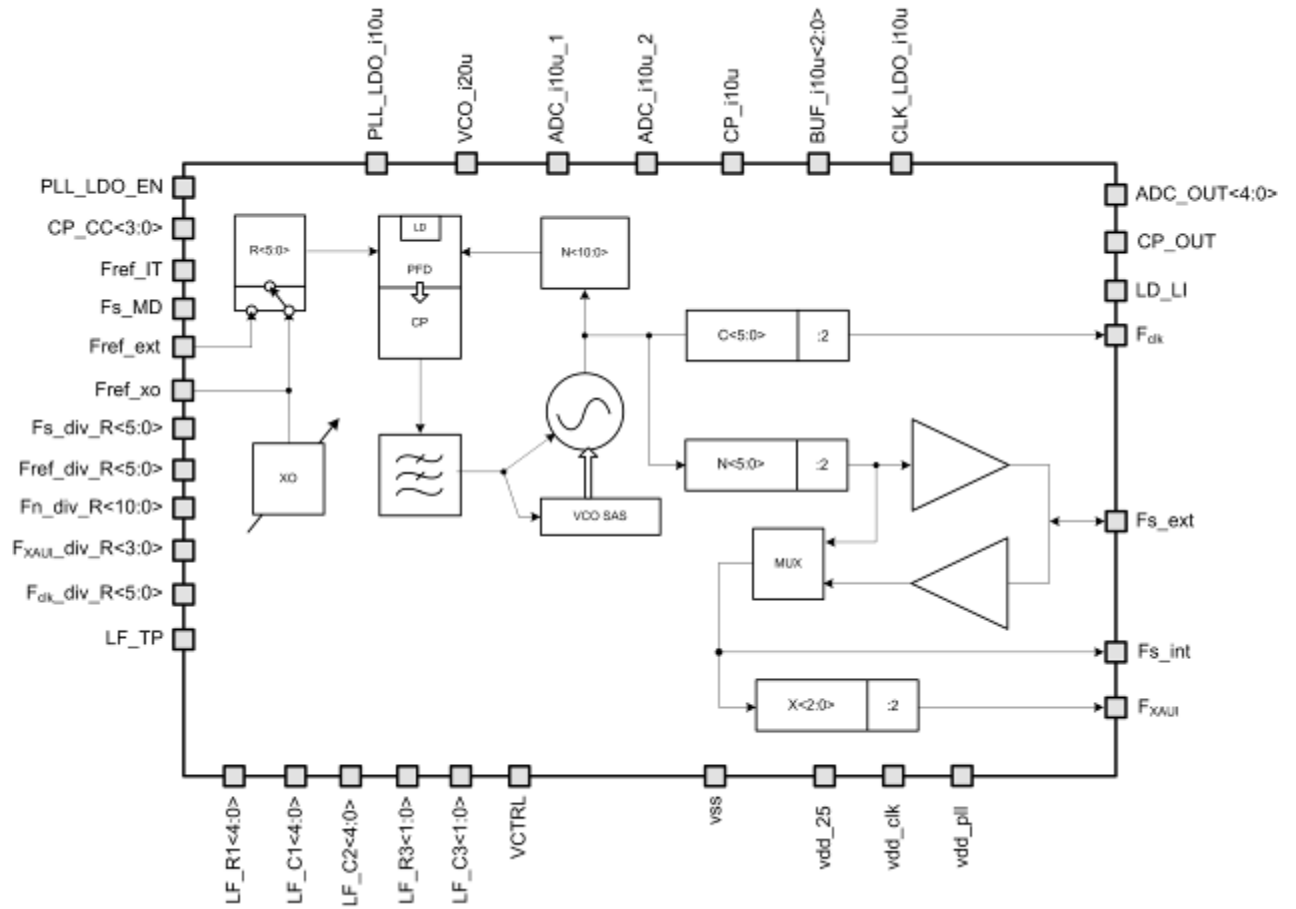


Figure 1: Phase-locked loop clock generator structure.

## 5 PIN DESCRIPTION

Name	Direction	Description
PLL_LDO_i10u	I	LDO voltage regulator reference current 10 uA
VCO_i20u	I	VCO reference current 20 uA
ADC_i10u_1	I	ADC reference current 10 uA line 1
ADC_i10u_2	I	ADC reference current 10 uA line 2
CP_i10u	I	Charge pump reference current 10 uA
BUF_i10u<2:0>	I	Reference currents 3x10 uA for duty cycle correction circuits
CLK_LDO_i10u	I	LDO voltage regulator reference current 10 uA
PLL_LDO_En	I	Enable/Disable of PLL low drop-out voltage regulator
CP_CC<3:0>	I	Charge pump output current adjustment
F <sub>ref_IT</sub>	I	External reference frequency type
Fs_MD<1:0>	I	Sampling frequency management
Fref_ext	I	External reference frequency input
Fref_xo	I	Internal reference frequency input
s_div_R<5:0>	I	FVCO/FS frequency ratio (2-126)
Fref_div_R<5:0>	I	Reference frequency division ratio (1-63)
Fn_div_R<10:0>	I	Reference frequency division ratio (4-2047)
Fxaui_div_R<3:0>	I	FVCO/FXAUI frequency ratio (1-14)
Fclk_div_R<5:0>	I	FVCO/FCLK frequency ratio (2-126)
LF_TP	I	PLL loop filter type
LF_R1<4:0>	I	PLL loop filter resistance R1 value adjustment
LF_C1<4:0>	I	PLL loop filter capacitance C1 value adjustment
LF_C2<4:0>	I	PLL loop filter capacitance C2 value adjustment
LF_R3<1:0>	I	PLL loop filter resistance R3 value adjustment
LF_C3<1:0>	I	PLL loop filter capacitance C3 value adjustment
VCTRL	I	VCO control voltage from external loop filter
ADC_OUT<4:0>	O	PLL Analog-to-digital converter output (digital value of VCO control voltage) Code interpretation
CP_OUT	O	Charge pump output for external loop filter circuit
LD_LI	O	Lock indicator
Fclk	O	CLK frequency output
Fs_ext	IO	Sampling frequency input/output node
Fxaui	O	XAUI frequency output
Fs_int	O	Sampling frequency output for internal circuits

Table "Pin description" (continue)

<b>Name</b>	<b>Direction</b>	<b>Description</b>
vss	IO	Ground
vdd_25	IO	External 2.5V power supply line
vdd_pll	IO	PLL power supply line (LDO voltage regulator output)
vdd_clk	IO	CLK power supply line (LDO voltage regulator output)

## 6 LAYOUT DESCRIPTION

The block dimensions are given in the table 1.

**Table 1:** Block dimensions.

Dimension	Value	Unit
Height	880	$\mu\text{m}$
Width	1080	$\mu\text{m}$

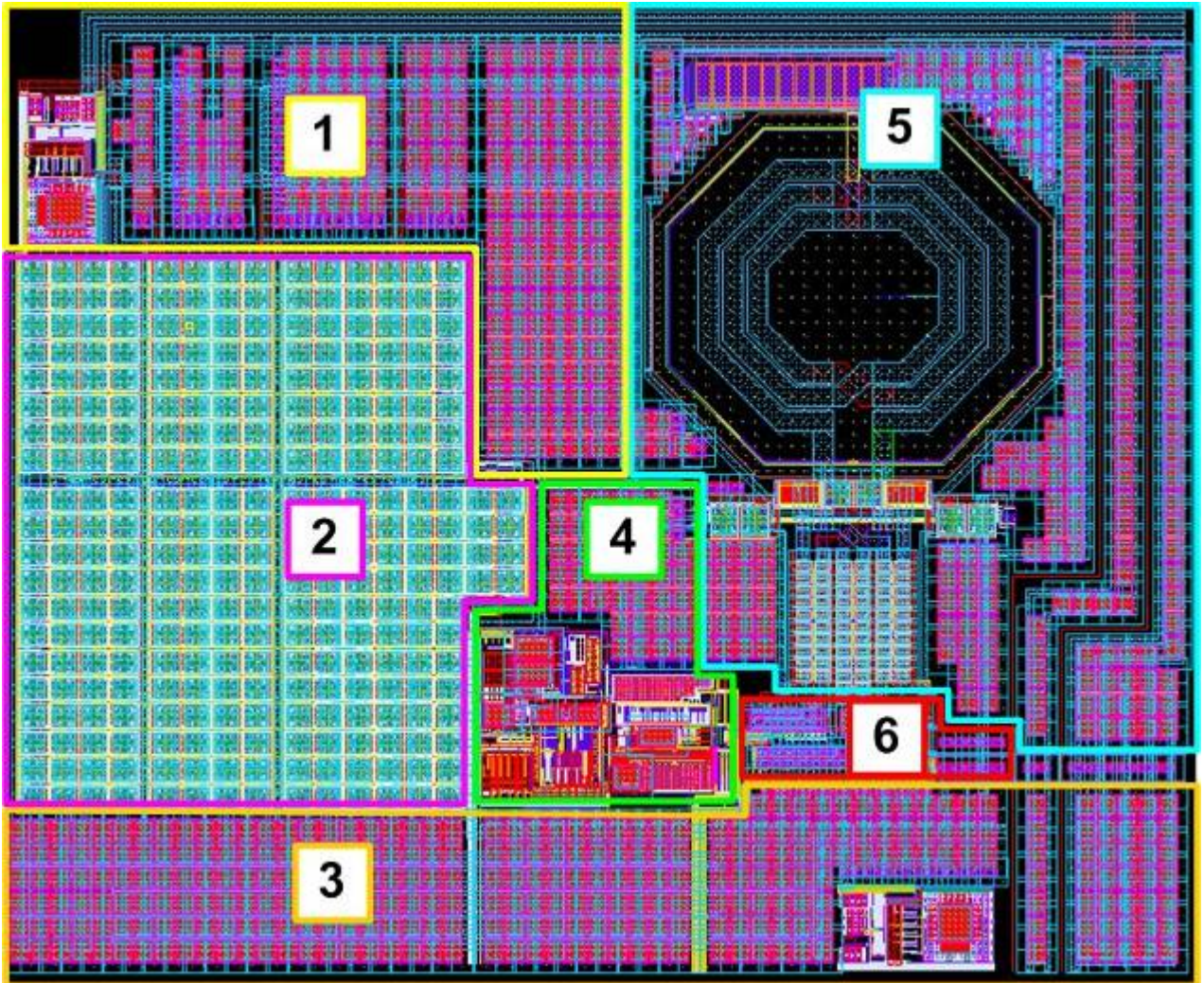


Figure 2: Device layout view.

1. PLL LDO voltage regulator
2. Loop filter
3. CLK LDO voltage regulator
4. Phase-frequency detector with Charge pump
5. VCO
6. Frequency dividers

## 7 OPERATING CHARACTERISTICS

### 7.1 TECHNICAL CHARACTERISTICS

Technology \_\_\_\_\_ TSMC CMOS CRN65LP  
 Status \_\_\_\_\_ silicon proven  
 Area \_\_\_\_\_ 0.95 mm<sup>2</sup>

### 7.2 ELECTRICAL CHARACTERISTICS

The values of electrical characteristics are specified for  $V_{dd,25} = 2.375 \div 2.625$  V and  $T = -40 \div +125^{\circ}\text{C}$ . Typical values are at  $V_{dd,25} = 2.5$  V,  $T = +85^{\circ}\text{C}$ , unless otherwise specified.

Parameter	Symbol	Condition	Value			Unit	
			min	typ	max		
Supply voltage	$V_{dd,25}$	-	2.375	2.5	2.625	V	
VCO control voltage	$V_{ctrl}$	-	0.5	-	2.0	V	
Internal regulated supply voltage	$V_{dd\_pll}$	From bandgap reference:				V	
		LDO preset=1.16V	1.144	1.164	1.182		
		LDO preset=1.20V	1.181	1.200	1.217		
		LDO preset=1.24V	1.221	1.241	1.257		
		LDO preset=1.28V	1.258	1.277	1.293		
Temperature range	T	-	-40	85	125	$^{\circ}\text{C}$	
VCO frequency range	$F_{vco}$	Typical case	1850	-	2140	MHz	
Internal reference frequency	$F_{ref\_int}$	-	-	25	-	MHz	
External reference frequency	$F_{ref\_ext}$	-	25	-	500	MHz	
Phase-detector frequency	$F_{pfd}$	-	-	-	250	MHz	
Phase noise	N	$F_s = 500\text{MHz}$	Frequency offset:			dB/Hz	
			10kHz	-	-97		-
			100kHz	-	-99		-
			1MHz	-	-124		-
		10MHz	-	-135	-		
Period jitter (rms)	J	$F_s = 500\text{MHz}$	-	2.12	-	ps	
Charge pump sink/source current value mismatch	$I_{cp\_mis}$	$0.5\text{ V} < V_{ctrl} < 2\text{ V}$	-	-	4	%	
Charge pump sink and source current matching	$I_{cp\_m}$	$0.5\text{ V} < V_{ctrl} < 2\text{ V}$	-	-	3	%	
Charge pump sink/source current value	$I_{cp}$	-	20	-	320	$\mu\text{A}$	
Internal loop filter R1 value	R1	-	5	-	82.5	kOhm	
Internal loop filter C1 value	C1	-	24	-	768	pF	
Internal loop filter C2 value	C2	-	3	-	96	pF	
$F_s$ frequency value	$F_s$	Full voltage swing 45..55% duty cycle	107	-	750	MHz	
$F_{XAUI}$ frequency value	$F_{XAUI}$	Full swing voltage 45..55% duty cycle	50	-	750	MHz	
$F_{clk}$ frequency value	$F_{clk}$	Reduced voltage swing 45..55% duty cycle	12	-	750	MHz	
Reference frequency divider ratio	$R_{div}$	-	1	-	31		
VCO frequency divider ratio	$N_{div}$	-	4	-	2047		
Standby current	$I_{st}$	Without input signal		<1		$\mu\text{A}$	
Current consumption with buffer	$I_{buf}$	-	-	30	-	mA	

Table “Electrical characteristics” (continue)

Parameter	Symbol	Condition	Value			Unit
			min	typ	max	
Input logic-high level	$V_{IH}$	-	$0.8V_{dd\_25}$		$V_{dd\_25}$	V
Input logic-low level	$V_{IL}$	-	0	-	0.2	V

## 8 TYPICAL CHARACTERISTICS

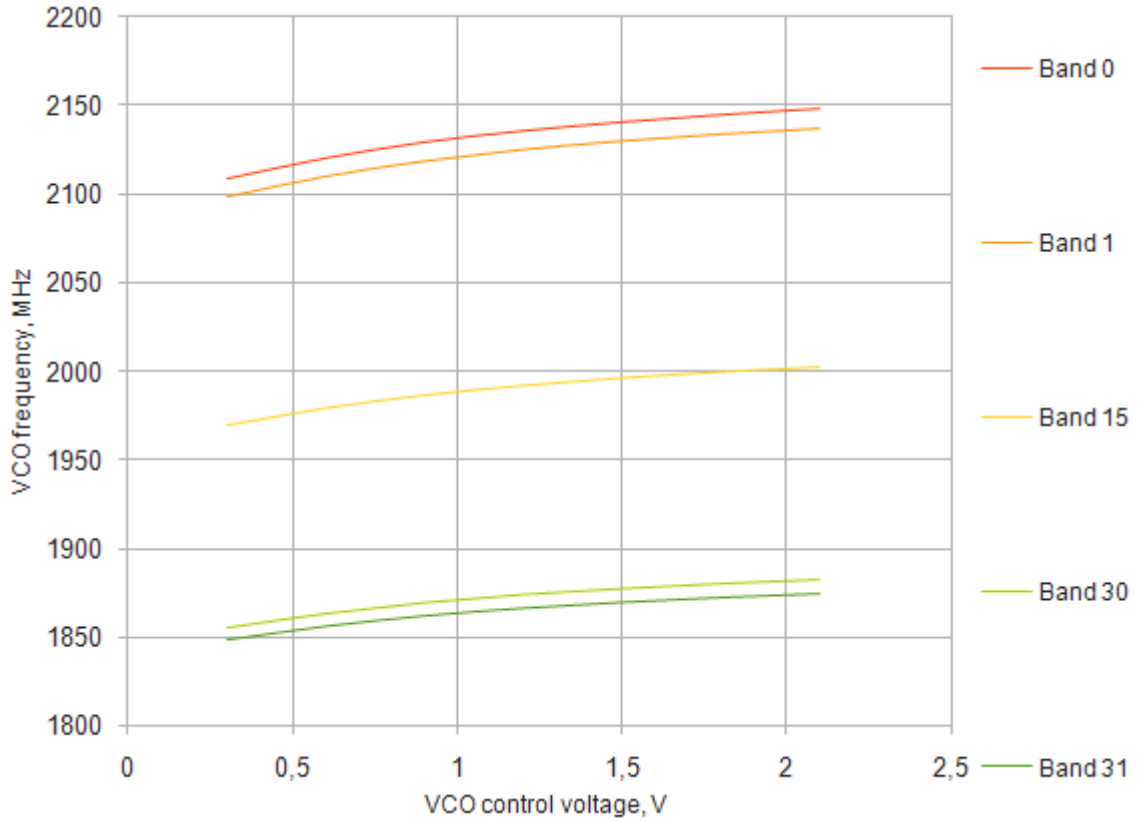


Figure 3: Simulated VCO tuning curves.

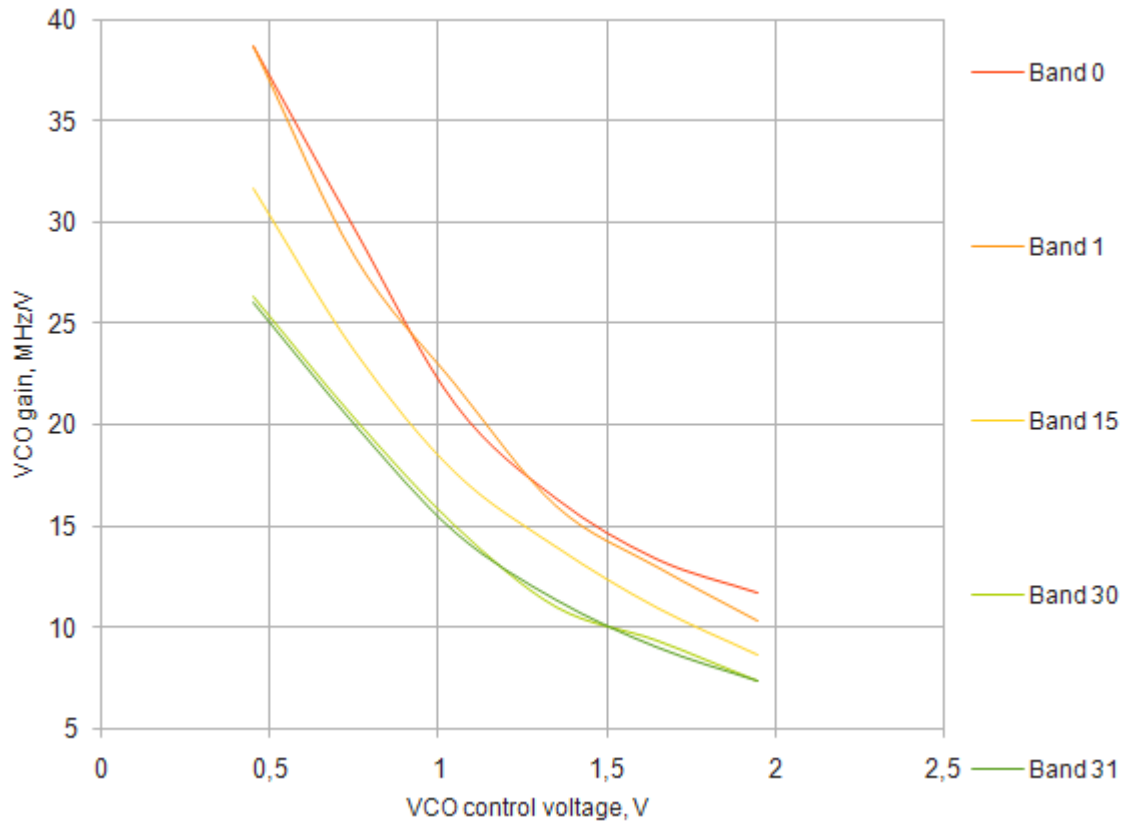


Figure 4: Simulated VCO gain.



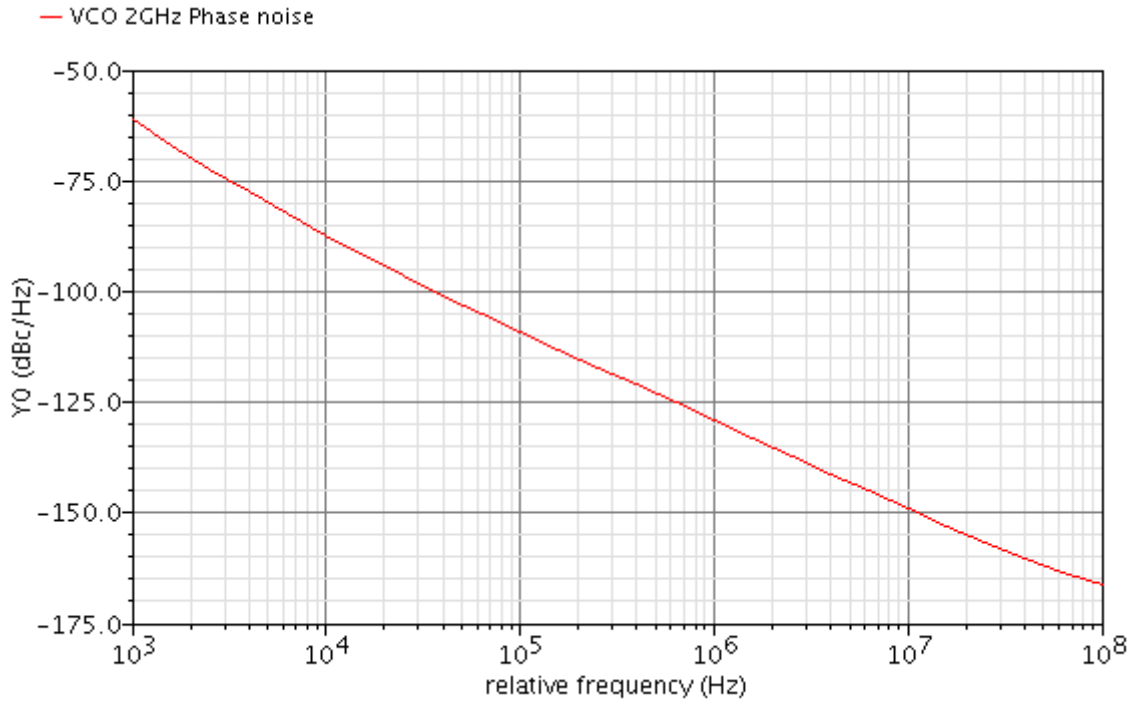


Figure 5: Simulated VCO open loop phase noise.

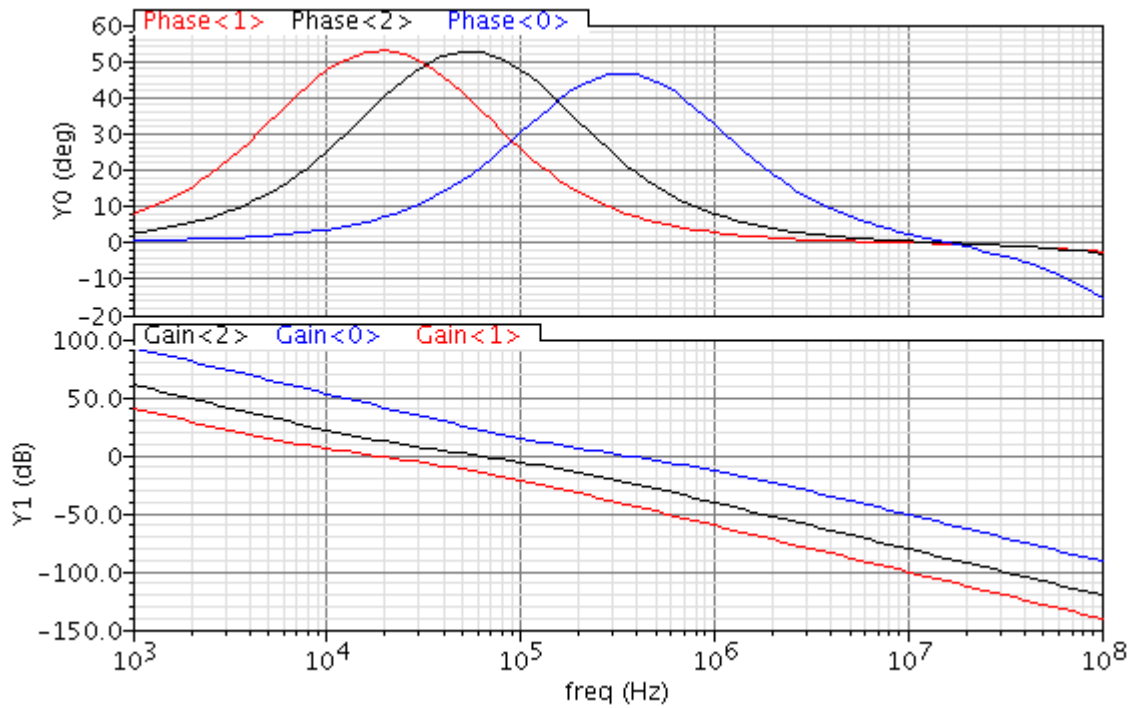
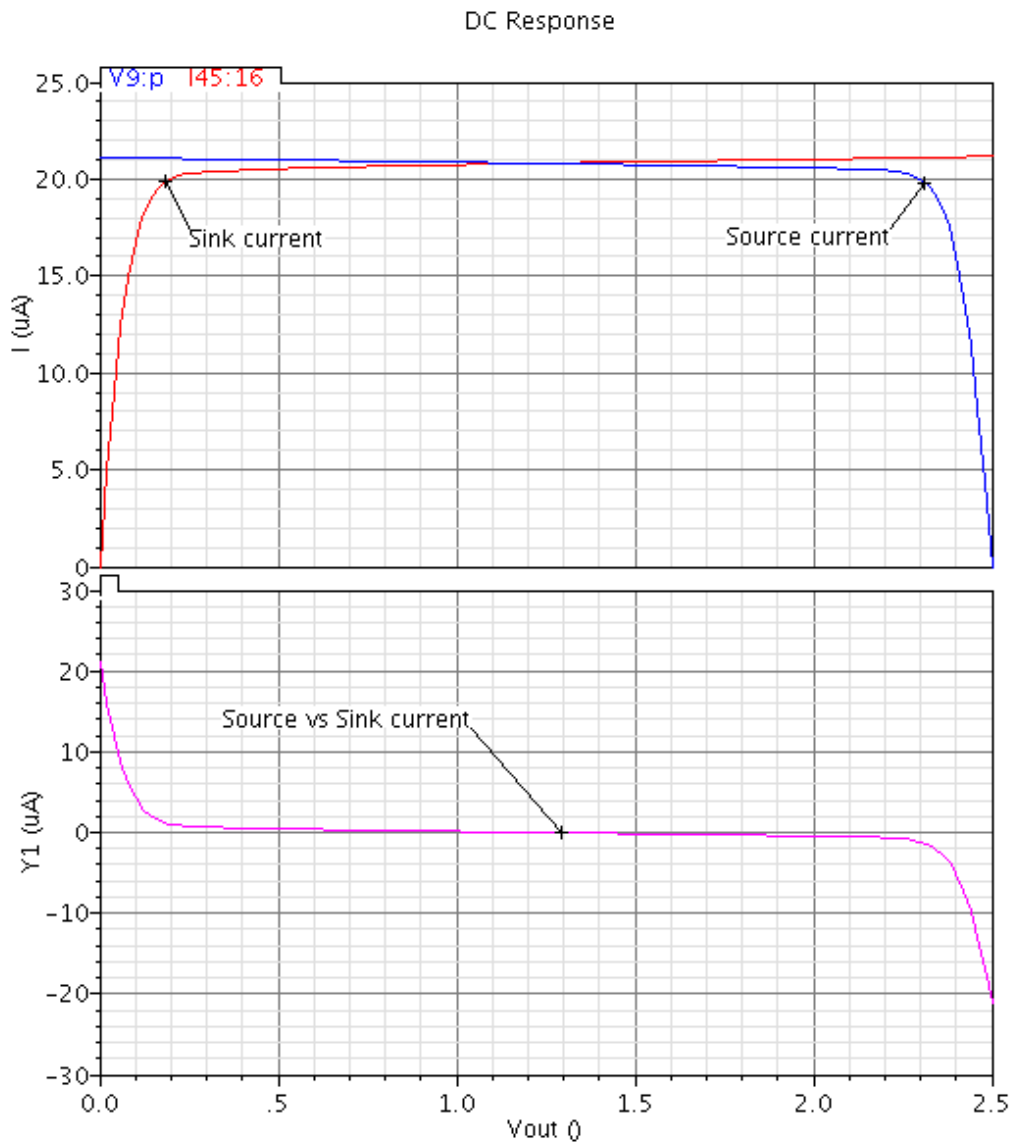


Figure 6: PLL open loop gain with minimum/center/maximum internal loop filter cutoff settings.



**Figure 7:** Charge pump output current (min current preset).

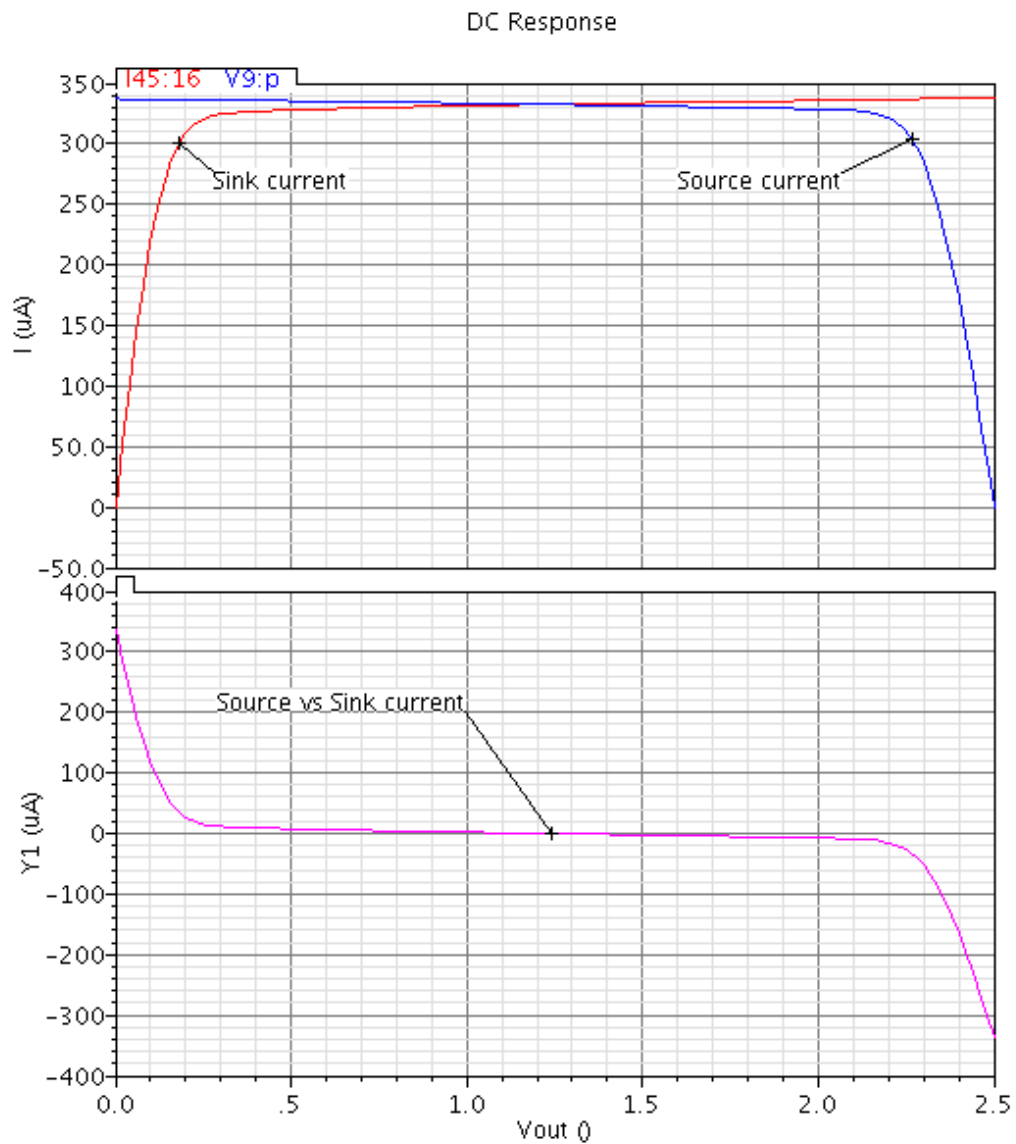


Figure 8: Charge pump output current (max current preset).

## 9 DELIVERABLES

IP contents:

- Schematic or NetList
- Layout or blackbox
- Extracted view (optional)
- GDSII
- DRC, LVS, antenna report
- Test bench with saved configurations (optional)
- Documentation